



MMBT2222A

**40V NPN SMALL SIGNAL TRANSISTOR IN SOT23** 

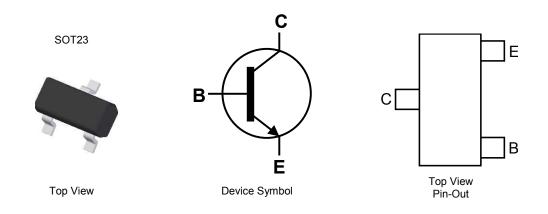
#### **Features**

- Epitaxial Planar Die Construction
- Low Saturation Voltage V<sub>CE(sat)</sub> < 300mV @ 150mA</li>
- Complementary PNP Type: MMBT2907A
- Ideal for Low Power Amplification and Switching
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen- and Antimony-Free. "Green" Device (Note 3)
- The MMBT2222AQ-7-F is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

## **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish; Solderable per MIL-STD-202, Method 208 3
- Weight: 0.008 grams (Approximate)



## Ordering Information (Note 4)

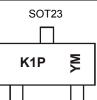
Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
MMBT2222A-7-F	Standard	K1P	7	8	3,000
MMBT2222A-13-F	Standard	K1P	13	8	10,000
MMBT2222AQ-7-F	Automotive	K1P	7	8	3,000

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**



K1P = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: H = 2020) M or  $\overline{M}$  = Month (ex: 9 = September)

Date Code Key						-						
Year	202	0 2	021	2022	2023	2024	2025	202	26 2	027	2028	2029
Code	Н			J	K	L	М	N		0	Р	R
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	Ν	D



# Absolute Maximum Ratings (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	75	V
Collector-Emitter Voltage	V <sub>CEO</sub>	40	V
Emitter-Base Voltage	V <sub>EBO</sub>	6.0	V
Collector Current	lc	600	mA
Peak Pulse Collector Current (single pulse)	Ісм	800	mA
Peak Pulse Base Current	I <sub>BM</sub>	200	mA

#### Thermal Characteristics (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Collector Dower Discipation	(Note 5)	D	310	mW	
Collector Power Dissipation	(Note 6)	P <sub>D</sub>	350		
Thermal Resistance, Junction to Ambient	(Note 5)	P	403	°C/W	
mermar Resistance, Junction to Ambient	(Note 6)	R <sub>θJA</sub>	357	C/W	
Thermal Resistance, Junction to Leads (Note 7)		R <sub>θJL</sub>	350	°C/W	
Operating and Storage Temperature Range	T <sub>J</sub> ,T <sub>STG</sub>	-55 to +150	°C		

## ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes: 5. For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.

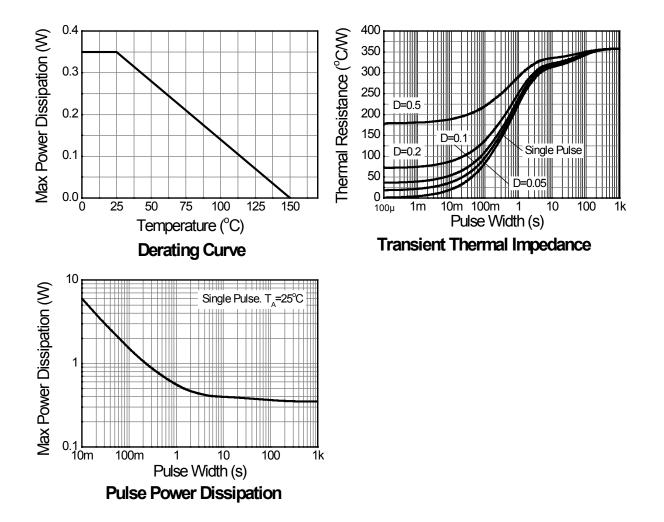
6. Same as Note 5, except the device is mounted on 15 mm x 15mm 1oz copper.

7. Thermal resistance from junction to solder-point (at the end of the leads).

8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



## **Thermal Characteristics and Derating Information**





## Electrical Characteristics (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS					
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	75	_	V	I <sub>C</sub> = 100μA, I <sub>E</sub> = 0
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	40	_	V	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	6.0		V	I <sub>E</sub> = 100μA, I <sub>C</sub> = 0
Collector Cut-Off Current	I <sub>CBO</sub>		10	nA μA	$V_{CB} = 60V, I_E = 0$ $V_{CB} = 60V, I_E = 0, T_A = +150^{\circ}C$
Collector Cut-Off Current	I <sub>CEX</sub>	_	10	nA	V <sub>CE</sub> = 60V, V <sub>EB(off)</sub> = 3.0V
Collector Cut-Off Current	ICEV		10	nA	V <sub>CE</sub> = 60V, V <sub>BE</sub> = ±0.25V
Emitter Cut-Off Current	I <sub>EBO</sub>		10	nA	V <sub>EB</sub> = 5.0V, I <sub>C</sub> = 0
Base Cut-Off Current	I <sub>BL</sub>		20	nA	V <sub>CE</sub> = 60V, V <sub>EB(off)</sub> = 3.0V
ON CHARACTERISTICS (Note 9)				•	
DC Current Gain	h <sub>FE</sub>	35 50 75 100 40 50 35	  300 	_	$\begin{split} I_{C} &= 100 \mu A, V_{CE} = 10V \\ I_{C} &= 1.0 m A, V_{CE} = 10V \\ I_{C} &= 10 m A, V_{CE} = 10V \\ I_{C} &= 150 m A, V_{CE} = 10V \\ I_{C} &= 500 m A, V_{CE} = 10V \\ I_{C} &= 10 m A, V_{CE} = 10V, T_{A} = -55^{\circ}C \\ I_{C} &= 150 m A, V_{CE} = 1.0V \end{split}$
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>		0.3 1.0	v	$I_{C}$ = 150mA, $I_{B}$ = 15mA $I_{C}$ = 500mA, $I_{B}$ = 50mA
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	0.6	1.2 2.0	V	$I_{C}$ = 150mA, $I_{B}$ = 15mA $I_{C}$ = 500mA, $I_{B}$ = 50mA
SMALL SIGNAL CHARACTERISTICS				•	·
Output Capacitance	C <sub>obo</sub>	_	8	pF	V <sub>CB</sub> = 10V, f = 1.0MHz, I <sub>E</sub> = 0
Input Capacitance	Cibo	_	25	pF	V <sub>EB</sub> = 0.5V, f = 1.0MHz, I <sub>C</sub> = 0
Transition frequency	f <sub>T</sub>	300	_	MHz	V <sub>CE</sub> = 20V, I <sub>C</sub> = 20mA, f = 100MHz
Noise Figure	N <sub>F</sub>	_	4.0	dB	$V_{CE}$ = 10V, I <sub>C</sub> = 100µA, R <sub>S</sub> = 1.0kΩ, f = 1.0kHz
SWITCHING CHARACTERISTICS	•			•	·
Delay Time	t <sub>d</sub>		10	ns	$V_{CC}$ = 30V, I <sub>C</sub> = 150mA, $V_{BE(off)}$ = - 0.5V, I <sub>B1</sub> = 15mA
Rise Time	tr		25	ns	$\label{eq:VCC} \begin{array}{l} V_{CC} = 30V, \ I_C = 150mA, \ I_{B1} = 15mA, \\ V_{BE(off)} = 0.5V \end{array}$
Storage Time	ts		225	ns	$V_{CC} = 30V, I_C = 150mA,$ $I_{B1} = -I_{B2} = 15mA$
Fall Time	t <sub>f</sub>		60	ns	V <sub>CC</sub> = 30V, I <sub>C</sub> = 150mA, I <sub>B1</sub> = -I <sub>B2</sub> = 15mA

Note: 9. Measured under pulsed conditions. Pulse width  $\leq$  300µs. Duty cycle  $\leq$  2%.





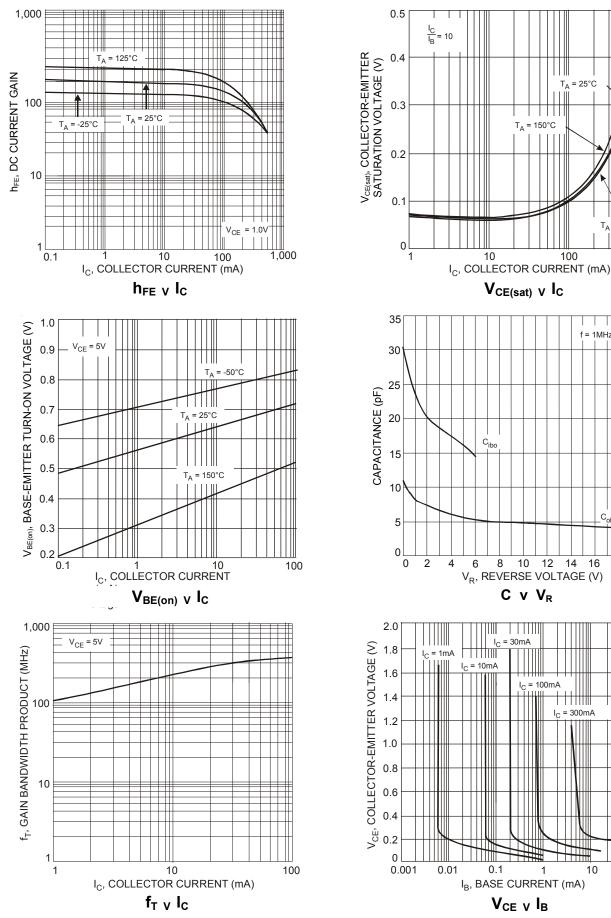
T<sub>A</sub> = -50°C

f = 1MHz

C<sub>obo</sub>

18 20

1,000



MMBT2222A Document number: DS30041 Rev. 17 - 2

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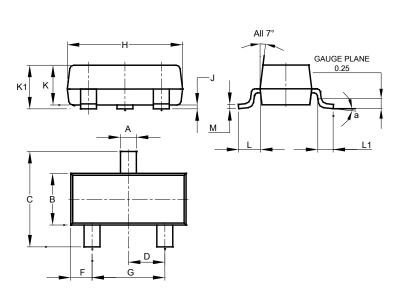
100

10



## Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.



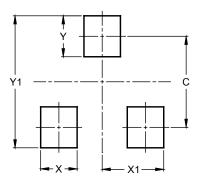
SOT23

SOT23

SOT23							
Dim	Min	Тур					
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
ĸ	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
а	0°	8°					
All	All Dimensions in mm						

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



 Dimensions
 Value (in mm)

 C
 2.0

 X
 0.8

 X1
 1.35

 Y
 0.9

 Y1
 2.9



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